

# PATENT ABSTRACTS OF JAPAN

(11)Publication number : 04-325500

(43)Date of publication of application : 13.11.1992

(51)Int.Cl. C30B 33/00  
H01L 21/02  
H01L 21/20

(21)Application number : 03-125560

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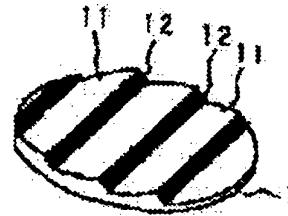
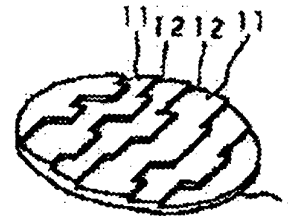
(22)Date of filing : 26.04.1991

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## (54) METHOD FOR CONTROLLING STRUCTURE OF CRYSTALLINE SURFACE

### (57)Abstract:

PURPOSE: To realize a semiconductor device controlled at an atomic level by manufacturing a crystalline substrate having a sufficiently wide terrace part required for device operation.  
CONSTITUTION: A crystalline substrate 1((a)) after surface polishing in which a terrace part 11 and a step part 12 are ununiformly distributed is subjected to growth by atomic layer epitaxy and is irradiated with light having spatial periodicity. The pattern of the terrace part 11 and the step part 12 is uniformized, and the step part 12 is multiplexed to spread the terrace part 11 ((b)).



## LEGAL STATUS

[Date of request for examination]

[Date of sending the examiner's decision of rejection]

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number]

[Date of registration]

[Number of appeal against examiner's decision of rejection]

[Date of requesting appeal against examiner's decision of rejection]

[Date of extinction of right]